

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	308306	(chalcogen\$4 sulfides selenides tellurides Ge-Sb-Te GeSbTe Ge near Sb near Te phase adj change PCM ovonic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:06
L2	9544536	(first bottom lower rear)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:07
L3	9192250	(second top upper front)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:07
L4	4638393	(electrode contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:08
L5	3328675	(((((\$3mos metal adj oxide) adj transistor) \$3fet \$2fet) (transistor switch\$4 tft) (fet mosfet mos cmos))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:16
L6	118223	(bl bitline bit adj line readline read adj line sense adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:23
L7	2463621	(common shar\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:29
L8	4245809	arra\$4 matrix crosspoint\$4 cross adj point\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:31
L9	8218	phase adj change near2 (material memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:33
L10	307691	(chalcogen\$4 sulfides selenides tellurides Ge-Sb-Te GeSbTe Ge near Sb near Te phase adj change PCM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:33

L11	442378	barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:33
L12	943	L11 near9 L10	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:33
L13	4638393	electrode contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:33
L14	203	L12 with L13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:33
L15	66	L14 and L9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:47
L16	13	((chalcogen\$4 sulfides selenides tellurides Ge-Sb-Te GeSbTe Ge near Sb near Te phase adj change PCM ovonic) AND (first bottom lower rear) AND (second top upper front) AND (electrode contact) AND (((((\$3mos metal adj oxide) adj transistor) \$3fet \$2fet) (transistor switch\$4 tft) (fet mosfet mos cmos)) AND (bl bitline bit adj line readline read adj line sense adj line) AND (common shar\$4)).CLM.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 08:47

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L17	12	((chalcogen\$4 sulfides selenides tellurides Ge-Sb-Te GeSbTe Ge near Sb near Te phase adj change PCM ovonic) AND (first bottom lower rear) AND (second top upper front) AND (electrode contact) AND ((((3mos metal adj oxide) adj transistor) \$3fet \$2fet) (transistor switch\$4 tft) (fet mosfet mos cmos)) AND (bl bitline bit adj line readline read adj line sense adj line) AND (common shar\$4)).CLM.	US-PGPUB	OR	ON	2005/12/05 08:49